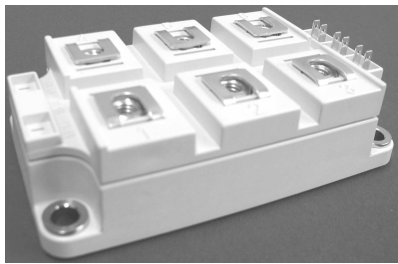


SKKR 200/0.2 BVR



SEMITRANS™ 5

Shunt Modules

SKKR 200/0.2 BVR

Features

- Low inductance value
- Excellent long term stability
- Isolated copper baseplate using DCB (Direct Copper Bonding) Technology
- Large clearance (13 mm) and creepage distance (20 mm)
- Using BVR Shunts for extended lifetime

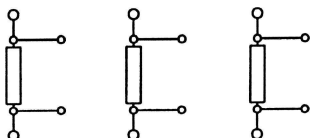
Typical Applications

- Current sensor for frequency converter

Absolute Maximum Ratings		T _c = 25 °C, unless otherwise specified	
Symbol	Conditions	Values	Units
I _{DCmax}	T _{shunt} = 150 °C; T _C = 25(80) °C	135 (100)	A
I _{SC}	t _{sc} = 10 μs	350	A
R _{shunt}	Toleranz = ± 5%	1,06	mΩ
T _{cr(shunt)}	temperature coefficient (20-60) °C	50	ppm/K
P _{tot}	per shunt; T _C = 25(80) °C	18 (10)	W
T _{stg}		- 40 ... + 125	°C
V _{isol}	AC, 1 min., I _{ISO} = 1 mA	2500	V
humidity	IEC-EN 60 721-3-3		
climate	IEC 68 T.1	40/126/56	

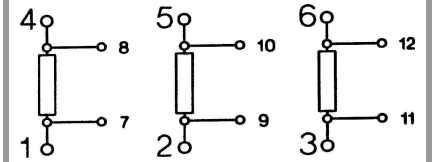
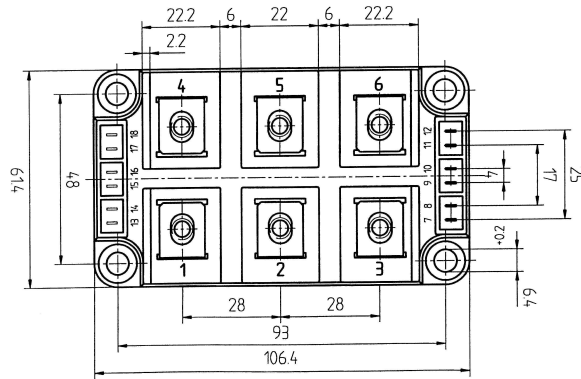
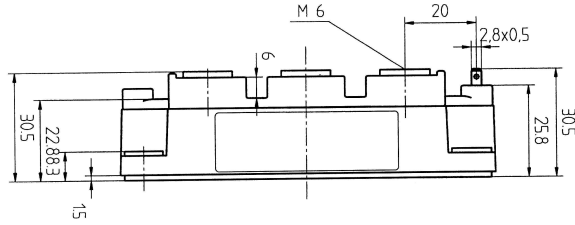
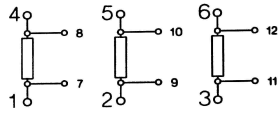
Characteristics		T _c = 25 °C, unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	Units
V ₇₋₈	IDC = 200 A; TC = 25(125) °C	210	213 (211)	216	mV
V ₉₋₁₀	IDC = 200 A; TC = 25(125) °C	210	213 (211)	216	mV
V ₁₁₋₁₂	IDC = 200 A; TC = 25(125) °C	210	213 (211)	216	mV
C _{shunt/C}			280		pF
L _{tray}	I _C = 100 A; V _{CE} = 600 V (turn off single IGBT)			0,4	nF
Thermal characteristics					
R _{th(j-c)}				7,0	K/W

Mechanical Data		min.	typ.	max.	Units
M ₁	to heatsink, SI Units (M6)	3		5	Nm
	to heatsink, US Units	27		44	lb.in.
M ₂	to heatsink, SI Units (M6)	2,5		5	Nm
	to heatsink, US Units	22		44	lb.in.
a				5x9,81	m/s ²
w				420	g



SKKR 200/0.2 BVR

Dimensions in mm



SKKR

Case D 97

Case D 97

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.